

Search History (9pp) ~~file~~ (6/12/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8	source near6 common adj ground and memory adj array.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:11
L2	31389	CD-ROM and Dvd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:12
L3	2	CD-ROM and Dvd and memory adj array and laser adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
L4	2	"5696714".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:13
L5	5611	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40
L6	0	I5 and (planari?ation planari?e) and (Si silicon semiconductor) adj thin adj film and (integrated adj circuit IC) adj2 (layer) and (light-emitting light adj emitting laser adj diode photodiode photodetect\$3 hall adj sensor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 20:42
S1	4	"743104".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 13:38
S2	1	(US-20040135157-\$).did.	US-PGPUB	OR	OFF	2005/05/24 11:53
S3	0	jp-60206889\$-\$-did.	US-PGPUB	OR	OFF	2005/05/24 11:54
S4	1	jp-60206889\$-\$-did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58

S5	2	jp-10063807\$-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/24 11:58
S6	152	(257/93).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S7	209	(257/501).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/11 19:50
S8	360	S6 S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S9	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 19:51
S10	1	S8 and (light adj emitting light-emitting) and (("without" "no") adj wire adj bond\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S11	127	S8 and (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S12	34	S8 and (light adj emitting light-emitting) and planar\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 19:54
S13	14	(US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US-5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$).did.	USPAT	OR	OFF	2005/06/11 20:11
S14	4	S13 and print\$3	US-PGPUB; USPAT	OR	OFF	2005/06/11 20:33
S15	5349	((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/06/12 20:40

S16	1	S15 and monolithic and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:39
S17	2	S15 and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43
S18	0	S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:43
S19	3	S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:45
S20	3	S15 and integrated adj circuit near6 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:46
S21	2	S15 and integrated adj circuit near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:47
S22	2	S15 and (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:48
S23	17	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 20:55
S24	154	(IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) and thin adj2 film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:04

S25	2	("5055907").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:26
S26	2	("4755866").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/11 21:30
S27	6922	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:31
S28	378	(light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 21:38
S29	189	(light-emitting light adj emitting LED laser adj diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:22
S30	249	semi-insulating adj substrate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:23
S31	249	semi-insulating adj substrate.ti. and semi-insulating	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:27
S32	3	semi-insulating adj substrate.ti. and semi-insulating near6 defined	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:33
S33	0	(silicon semiconductor semi-insulating) adj substrate near4 "having" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35
S34	0	(silicon semiconductor semi-insulating) adj substrate near4 "wherein" near4 (driver integrated)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:35

S35	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near4 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S36	0	(silicon semiconductor semi-insulating) adj substrate near10 "wherein" near10 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S37	1481	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:36
S38	72	(silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) and planariz\$5 and (LED light-emitting light adj emitting laser adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:51
S39	4756	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:52
S40	3231	(silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:53
S41	444	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/11 23:56
S42	317	(silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02
S43	54	(silicon semiconductor) adj substrate and thin adj2 film and planariz\$5 adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 00:02
S44	2	"5492851".pn. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:03

S45	2	"4902637".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 16:20
S46	0	(integrated adj circuit adj layer IC adj layer) and (planarization planarize) and (light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:11
S47	0	(integrated adj circuit adj layer IC adj layer) and (planarization planarize) and (thin adj2 film light-emitting light adj emitting diode) adj array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:12
S48	79	(integrated adj circuit adj layer IC adj layer) and (planarization planarize) and (thin adj2 film light-emitting light adj emitting diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:22
S49	15	(US-20050087817-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20040016976-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20030067043-\$).did. or (US-6903427-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US-6690845-\$ or US-6684007-\$ or US-6611635-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/06/12 15:22
S50	4	S49 and thin adj film near5 planarize\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:57
S51	0	S49 and thin adj film near5 planarize\$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:25
S52	4	S49 and thin adj film near5 planarize\$5 and (IC adj layer integrated adj circuit adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:28
S53	4	S49 and thin adj film near5 planarize\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:45

S54	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:50
S55	0	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and vcsel adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:51
S56	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:52
S57	4	S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer and (planari?e planari?ation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:53
S58	15	S49 and planariz\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58
S59	0	S49 and planariz\$5 and integrated adj circuit adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/12 15:58
S60	15	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 15:58
S61	15	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00
S62	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:00

S63	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S64	4	S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall laser adj diode photodetect\$3: photodiode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 16:01
S65	15	IC adj layer near6 stack\$3 and (planari?ation planari?e) and (EO LED light-emitting light adj emitting laser diode vcsel photodiode photodetect\$3 hall adj sensor piezo-electric piezoelectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:24
S66	29	cd-rom near4 diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 18:37
S67	5991	memory adj device and memory adj cell adj array and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S68	2403	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S69	1206	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 17:25
S70	687	memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S71	0	memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	USPAT	OR	ON	2005/06/12 17:26
S72	0	memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:26

S73	0	memory adj device and memory adj cell adj array.ti,ab,clm. and (GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S74	0	memory adj device and memory adj cell adj array.ti,ab,clm. and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S75	0	memory adj device and memory adj cell adj array and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:27
S76	45	memory adj device and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:33
S77	5	memory adj device and (SiC) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S78	39	memory adj device and (GaAs) adj substrate.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/12 17:34
S79	12	config-dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/12 20:01